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| FORM PTO 1449 (modified)  U.S. DEPARTMENT OF COMMERCE BATENT AND TRADEMARK CERCE 1/6 9 0 1006 |  |   |  |                 | ATTY DOCKET NO. APPLICATION NO. 10/533,091                |       | 91                                     |  |  |
|   |  | PATEN   | IT AND TRADEMARK OFFICE  | dron i de       | APPLICANT   |       |  |  |  |
| LIST OF REFERENCES CITED BY APP (BANT(S) (Use several sheets if necessary)                    |  |   |  |                 | HIDEYA KUMOMI, ET AL.                                     |       |  |  |  |
| . (535  |  |   | O TRADE  |                 | FILING DATE April 28, 2005                                |       | GROUP <b>2812</b>                      |  |  |
|   |  |   |  |                 | U.S. PATENT DOCUMENTS                                     |       | •                                      |  |  |
| *EXAMINER<br>INITIAL  |  |   | DOCUMENT<br>NUMBER   | DATE            | NAME  | CLASS | SUBCLASS                               | FILING DATE                            |  |
| A   | 2  |   | 5,130,103  | 07/14/92        | Yamagata et al.   | 428   | 209                                    |  |  |
|   |  |   | 5,207,863  | 05/04/93        | Kumomi  | 156   | 603                                    |  |  |
|   |  |   | 5,290,712  | 03/01/94        | Sato, et al.  | 437   | 24                                     | · · ·                                  |  |
| <u> </u>  | TT.  |   | 5,723,348  | 03/03/98        | Kumomi et al.   | 437   | 23                                     |  |  |
|   |  |   |  |                 |   |       |  |  |  |
| FOREIGN PATENT DOCUMENTS  |  |   |  |                 |   |       |  |  |  |
|   |  |   | DOCUMENT<br>NUMBER   | DATE            | COUNTRY   | CLASS | SUBCLASS                               | TRANSLATION<br>YES/NO/<br>OR ABSTRACT* |  |
| LA  | <u> </u>   | JP  | 8-8197   | 01/12/96        | Japan   | _     | _                                      | Abstract                               |  |
|   |  | <u> </u>  |  |                 |   |       |  |  |  |
|   |  |   |  |                 |   |       |  |  |  |
|   |  |   |  |                 |   |       |  |  |  |
|   |  | ·   | 01   | THER DOCUMENT(S | 6) (Including Author, Title, Date, Perlinent Pages, Etc.) |       |  | ***                                    |  |
|   | AR   | Kumomi, et al. "Selective Nucleation-based Epitaxy (SENTAXY): A novel Approach for Thin Film Formation"; JPN J. Appl. Phys., Vol. 36 pp 1383-1388 (1997). |  |                 |   |       |  |  |  |
|   | 1  |   | Kumomi, et al. "Fundamentals for the Formation and Structure Control of Thin Films: Nucleation, Growth, Solid-state Transformations"; Handbook of Thin Film Materials, Vol. 7, Ch. 6, pp 319-373 (2002). |                 |   |       |  |  |  |
|   |  |   | Hatano, et al. "Exclmer Laser-induced Temperature Field in Melting and Resolidification of Silicon Thin Films"; J. Appl. Phys., Vol. 87, No. 1, pp. 36-43 (2000).  |                 |   |       |  |  |  |
| A   | Van der Wilt, et al. "Formation of Location-controlled Crystalline Islands Using Substrate-embedded Seeds in Excimer-laser Crystallization of Silicon Films"; Appl. Phys. Lett, Vol. 79, No. 12, pp 1819-1821 (2001) |   |  |                 |   |       |  |  |  |
| FXAN  | MINER  |   | 121/2  |                 | DATE CONSIDERED 09/20/07                                  |       | ······································ |  |  |

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<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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FORM PTO 1449 (modified) ATTY DOCKET NO. APPLICATION NO. : National Stage of 03500.017731 U.S. DEPARTMENT OF COMMISSION OFFICE HIDEYA KUMOMI APPLICANT: LIST OF REFERENCES CITED BY APPLICANT(S)
(Use several sheets if necessary) FILING DATE April 28,2005 GROUP 2812 U.S. PATENT DOCUMENTS \*EXAMINER DOCUMENT FILING DATE INITIAL NUMBER DATE NAME CLASS SUBCLASS 4.564.403 1/1986 Hayafuji et al. 148 171 4,670,088 6/1987 Tsaur et al. 156 617 5,021,119 6/1991 Fan et al. Kumomi et al. 5.318.661 6/1994 ablaFan et al. 5,453,153 9/1995 5,496,768 3/1996 Kudo, T. 437 174 6,326,286 12/2001 Park et al. 2003/003766 1/2003 Kumomi et al. FOREIGN PATENT DOCUMENTS TRANSLATION YES/NO/ OR ABSTRACT DOCUMENT NUMBER DATE COUNTRY CLASS SUBCLASS **GB** Corresp to 2338342 12/199 **United Kingdom** USP 6,326,286 EP Corresp to 0472970 3/1992 Europe USP 5,318,661 EP Corresp. to 1262578 12/2002 Europe 2003/003766 WO Corresp. to UPS 5,021,119 89/04550 5/1989 PCT and 5,453,153 OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.) Kuriyama et al., "Comprehensive Study ... Thin Film Transistors", Jpn. J. Appl. Phys., Vol. 33, (Part 1, No. 10) (1994) 5657-5662. M Van Der Wilt, "Grain Location ... Thin Silicon Film", Phys. Stat. Solidi Vol. 166 No. 2, 619-626 (April 1998). Kumomi et al., "Manipulation of nucleation sites ... Si Crystallization", Appl. Phys. Ltts., Vol. 59, No. 27, 3565-3567 (Dec. 1999). Hatano et al.; "In situ and ex situ ... laser annealing", J. Non-Cryst. Solids, Vol. 266-269, 654-658 (May 2000) Patent Abstracts of Japan, Vol. 0080, No. 52 (C-213) 3-1984 for JP 58-208297 Patent Abstracts of Japan, Vol. 0172, No. 53 (E-1367) 5-1993 for JP04-373171 A)/L Patent Abstracts of Japan, Vol. 0164, No. 99 (E-1290) 10-1992 for JP04-184918 09/2010> **EXAMINER** DATE CONSIDERED EXAMINER: Initial if reference considered, whele of this form with next communication to applicant. ed, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy

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